

IN THE SPECIFICATION

Please rewrite the paragraph on page 8, lines 1-4 as follows:

Q1 The operation of the first mode of the invention is explained, referring to the timing chart as shown in Figure 1, concerning about the interlace solid-state image pickup device with the vertical OFD for the blooming control. The structure of the interlace solid-state image pickup device is explained, referring to Figures 7 to 9, 9 and 12.

Please rewrite the paragraph on page 9, lines 3-7, as follows:

Q2 The electric potential ϕ' is preferably deeper than ϕ_{tg} which ϕ_{tg} , the potential of the signal read-out portion 120, is given caused by the voltage VM_{cl} which is applied, during the times except the read-out step, to second charge transfer electrode 106 in signal read-out portion 120 adjacent to photo-electric conversion unit ~~101~~. 101 as shown in Figure 12.